

Ps formation, cooling and emission into vacuum from porous materials

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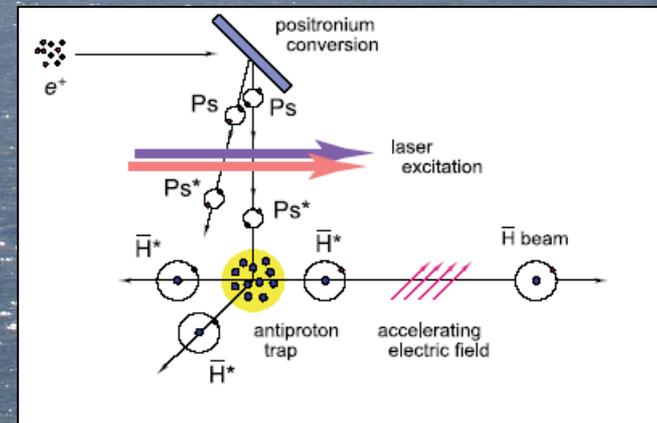


Positron in Astrophysics 19 march 2012 – Murren

main motivation

Many experiments with positrons require high yield of cooled Ps

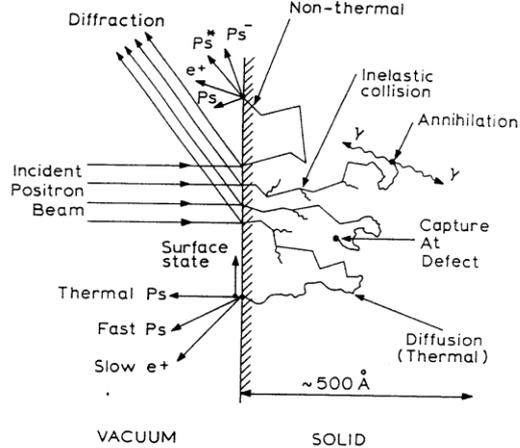
In particular we need cooled Ps for AEGIS Hbar experiment and Ps spectroscopy at CERN



Outline

- **Positronium emission from surface**
 - **Ps collisional cooling and Ps thermalization in porous material**

Ps at surfaces

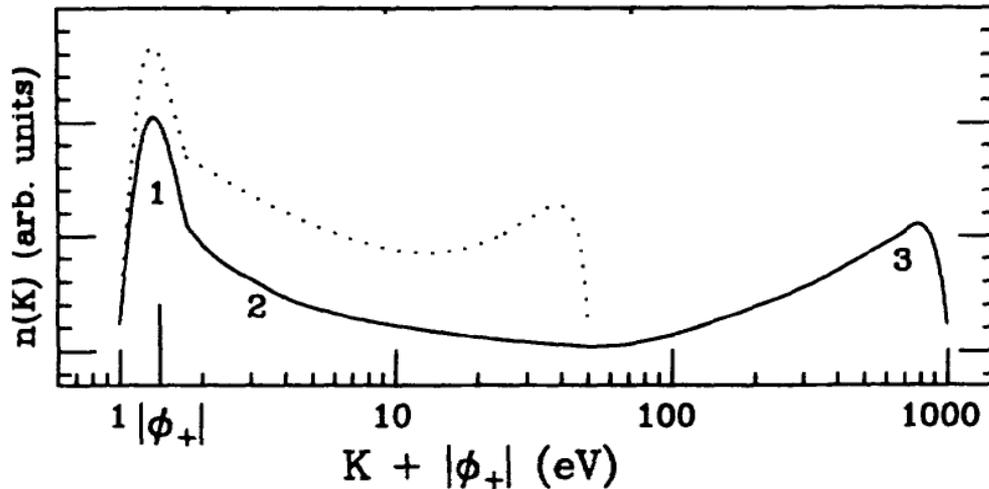


e^+ (0.1-20 keV)

Backscattered Ps

Hot Ps, Ps^* from epithermal e^+

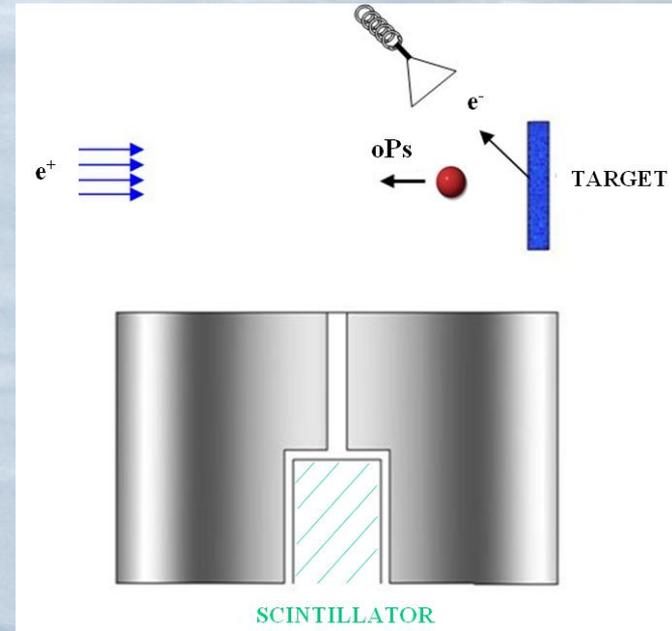
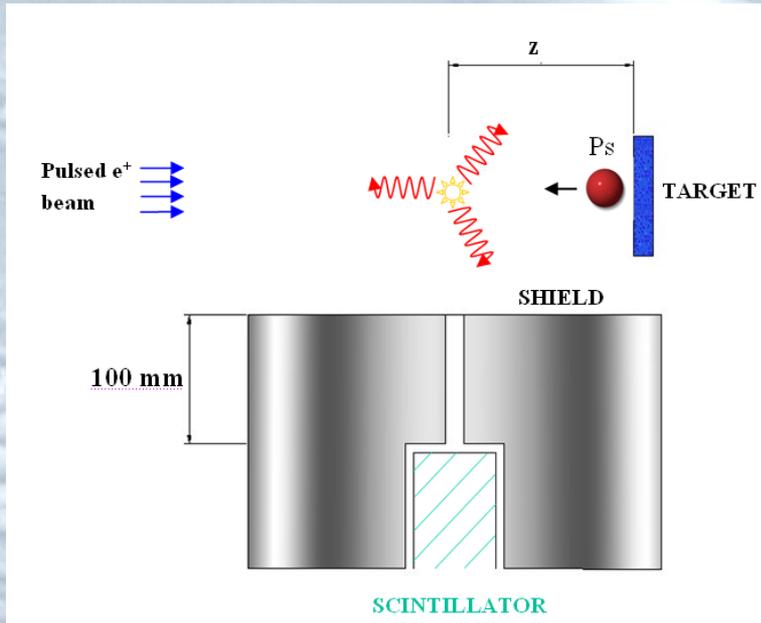
Hot Ps,
Thermal Ps from thermal e^+



Calculated density of e^+ returning at the Al surface, solid line 1keV e^+
dashed line 50 eV e^+

- 1 Thermal e^+
- 2 Epithermal e^+
- 3 Backscattered e^+

Time of flight measurement with e⁺ beams

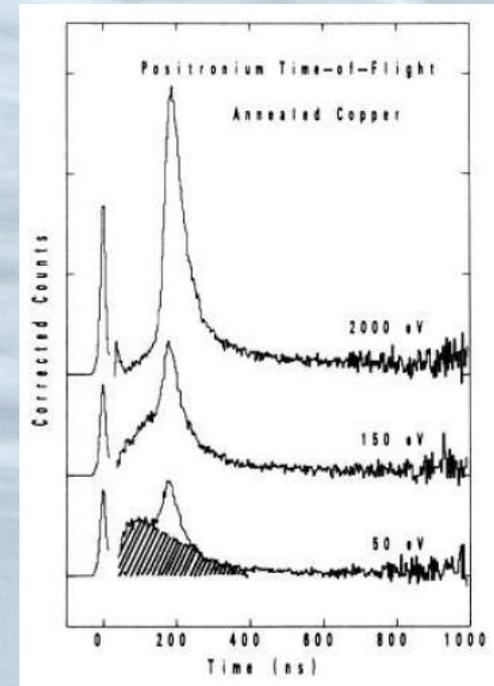
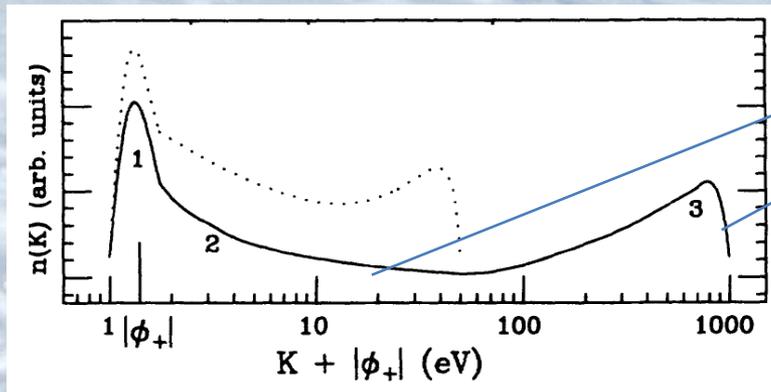


The perpendicular velocity is measured

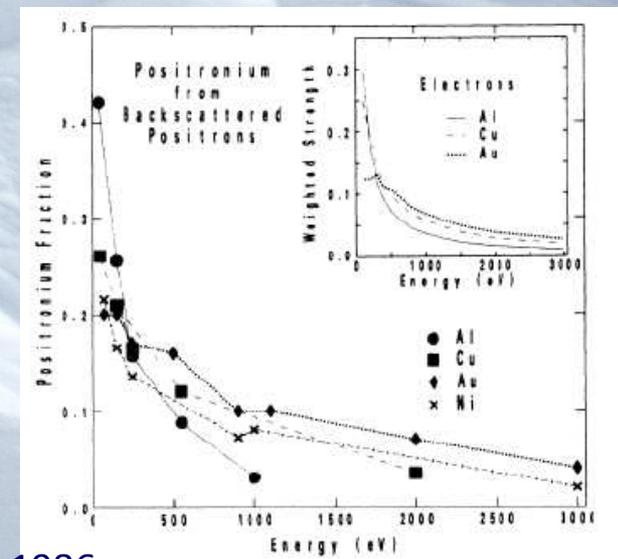
$$v_{\perp} \quad E_{\perp} = \frac{1}{2} m_{Ps} v_{\perp}^2 = m_e \frac{z^2}{t^2}$$

Backscattered Ps and Ps by epithermal e⁺

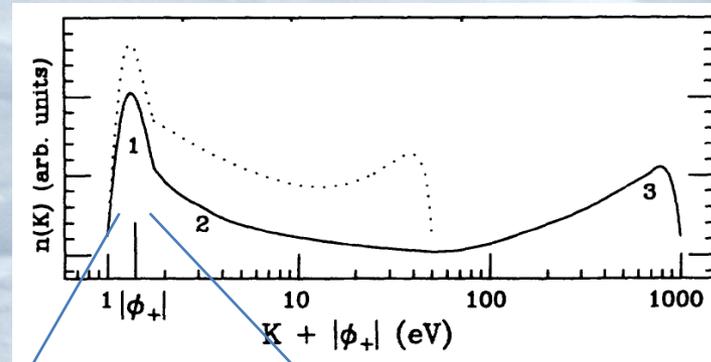
TOF spectra of Ps emitted from Cu
 Hatched area, spectrum of Ps from
 epithermal e⁺



Backscattered Ps has an energy dependence
 approximately as E^{-1} where E is the e⁺ incident
 energy



Ps formation and emission by thermal e^+



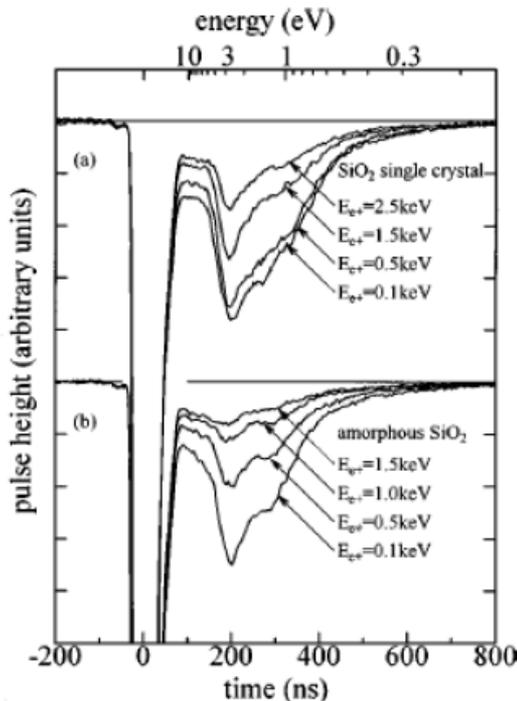
Direct Ps formation

Ps formation by trapped positron at the surface

Ps emission from dielectrics

- Ps formation by thermal positron reaching the surface is, in most cases, energetically forbidden. The 6.8 eV energy gain of Ps formation is not enough to extract an electron
- Formation of Ps can occur in the bulk. Ps reaching the surface can be emitted if its work function is negative

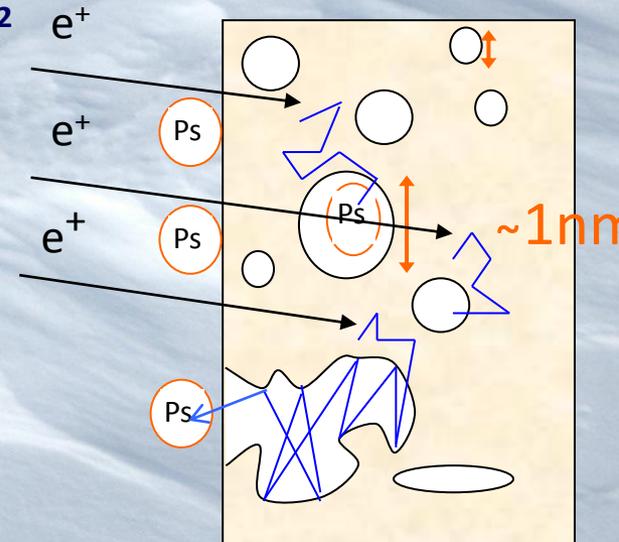
$$\varphi_{Ps} = \varphi_+ + \varphi_- - E_{gap} + E_b - 6.8 \text{ eV} < 0$$
- Ps can form and be hosted by open volumes in dielectrics. If there is an open volume defect network, hopping diffusion may lead to Ps emission into vacuum



In quartz and amorphous SiO₂ two different Ps components were observed :

One around 1 eV attributed to Ps formed in the bulk

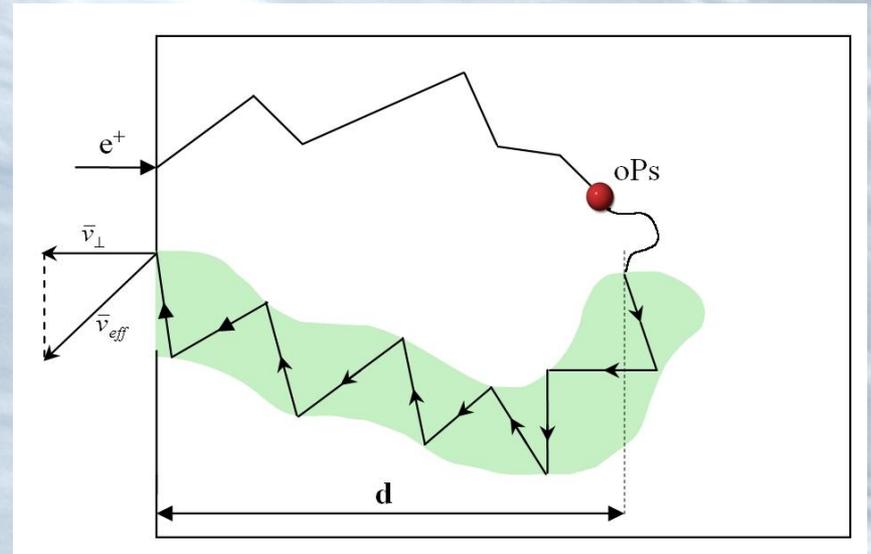
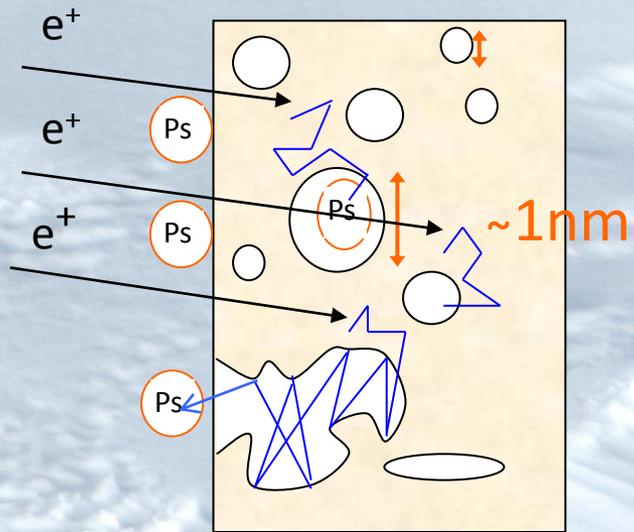
One around 3 eV by electron capture of an electron at The surface



Ps cooling using porous SiO_2 based materials



Ps cooling by collisions



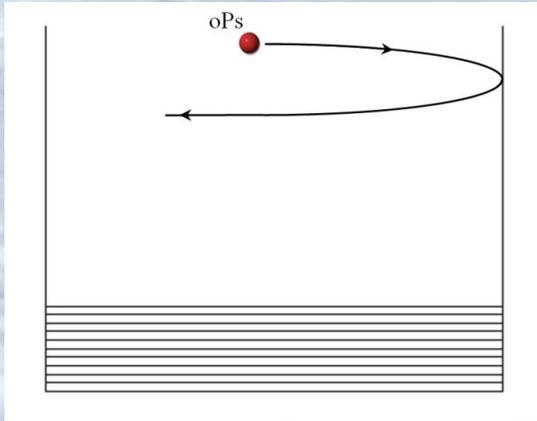
Ps is formed with eV energy but lose energy by collision with the walls of the connected porosities.

Ps energy is normally insufficient for electronic excitation, Ps lose energy by exciting atomic motion

A fraction of oPs can reach the surface and can be emitted cooled into the vacuum.

Ps cooling and quantum confinement

Ps cooling process can be described in two regimes:



HIGH ENERGY LIMIT:

de Broglie wavelength is small respect to the dimension d of the cavity

$$E \gg \frac{h^2}{4m_o d^2} \cong \left(\frac{6nm}{d} \right) 20 \text{ meV}$$

Ps can be considered a free object of size:

$$\lambda \cong 6 \text{ nm} \sqrt{\frac{20 \text{ meV}}{E}}$$

Ps collisions can be treated as a classical elastic scattering

(Sauder, *J. Res. Natl. Bur. Stand.* § A, **72**, (1968) 91)

Ps cooling and quantum confinement

LOW ENERGY REGIME $E < \frac{h^2}{4m_o d^2} \cong \left(\frac{6nm}{d} \right) 20 \text{ meV}$

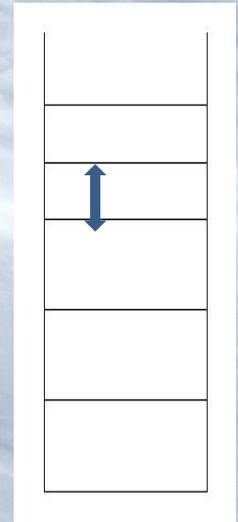
The interaction between the Ps atom and the walls can be described in terms of the contact between a confined Ps atom with the solid as a whole.

An estimation of the minimum T permitted for a Ps atom confined in nano-pores and nano-channels, when the temperature is lowered, can be made by modeling the Ps cooling by creation and destruction of phonons at the surface of the pores.

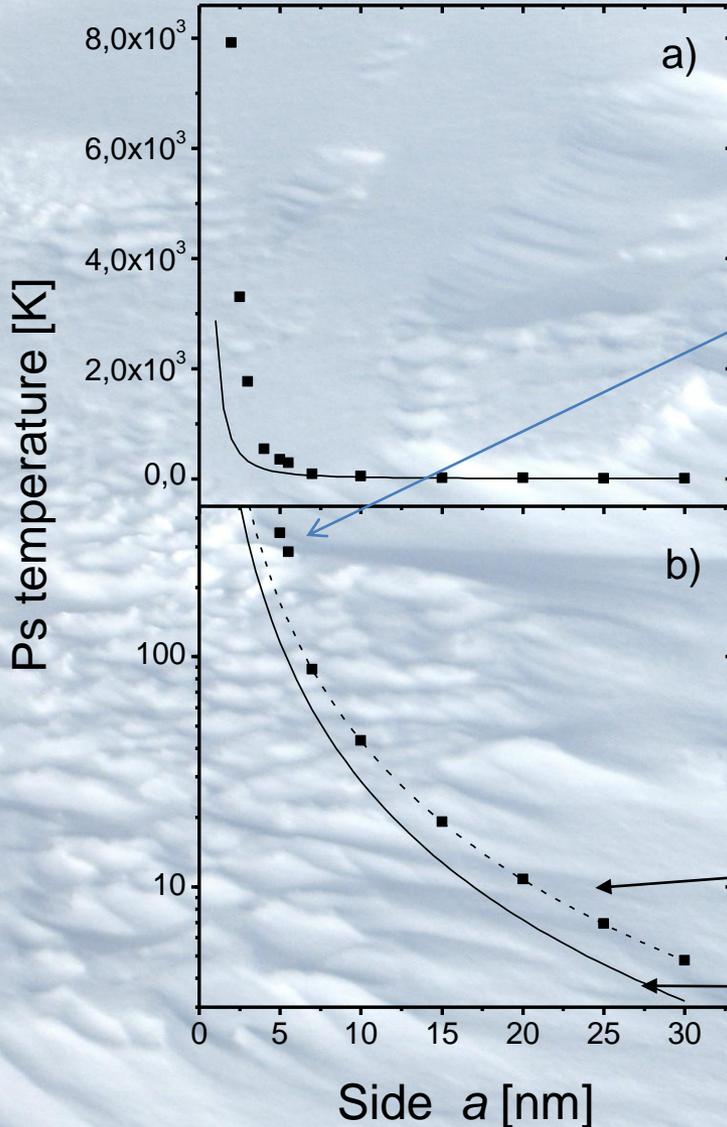
(Mariazzi ,Salemi, Brusa, PRB 2008).

the maximum variation of the momentum magnitude of Ps due to the exchange of a single phonon at the first order

$$\Delta k_{\max} = \left\| |k| - |k^I| \right\|_{\max} = \frac{2v_s m}{\hbar} \approx 1.7 * 10^8 \text{ m}^{-1}$$



Ps cooling and quantum confinement



Minimum energy and minimum temperature of a Ps atom confined in a cubic box of size a

$$E = \frac{\hbar^2 \pi^2}{2m} \left(\frac{n_m}{a}\right)^2$$

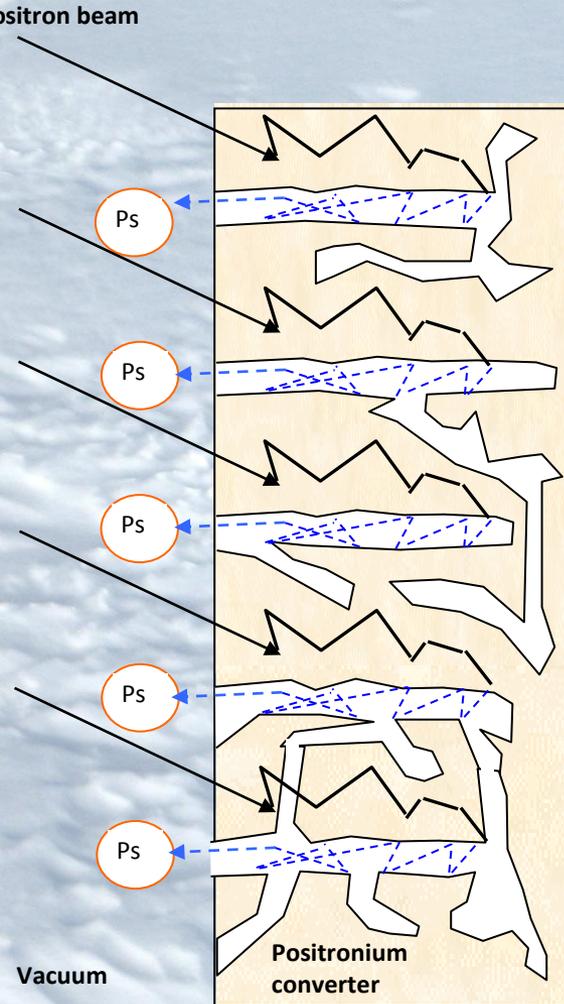
$$T = \frac{2}{3k_B} E = \frac{\hbar^2 \pi^2}{3k_B m} \left(\frac{n_m}{a}\right)^2$$

n_m is the lower accessible level

Dashed line : ground level in a cubic box

Continuous line : ground state = minimum level in Nano-channels (infinite well)

Nano-size and Ps thermalization

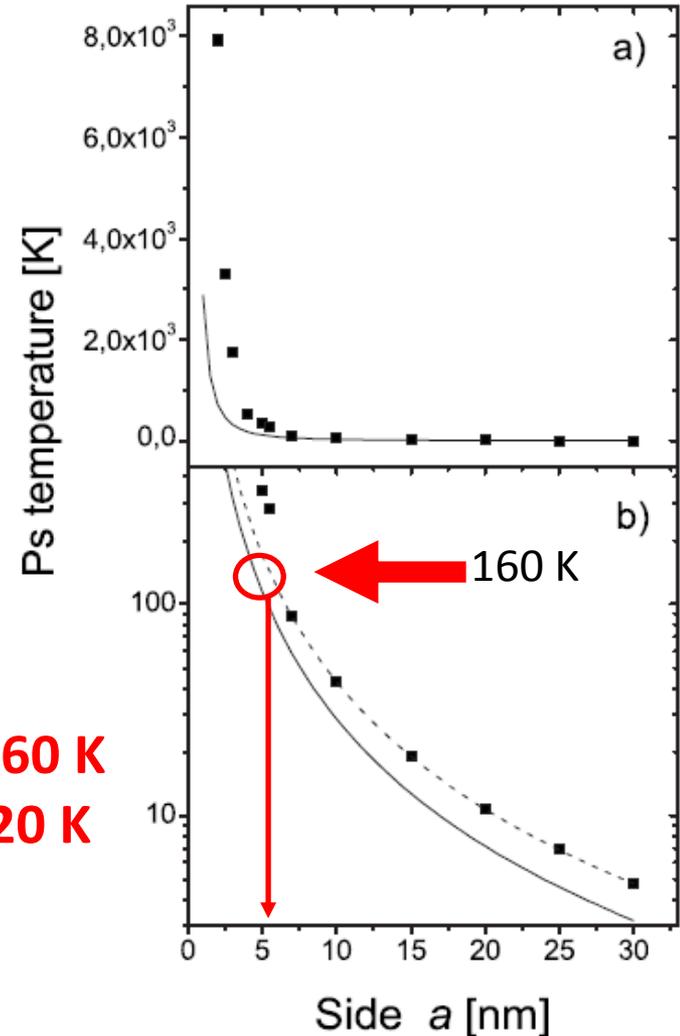


$$E_g = (\hbar^2 \pi^2) / (m a^2)$$

the minimum temperature is:

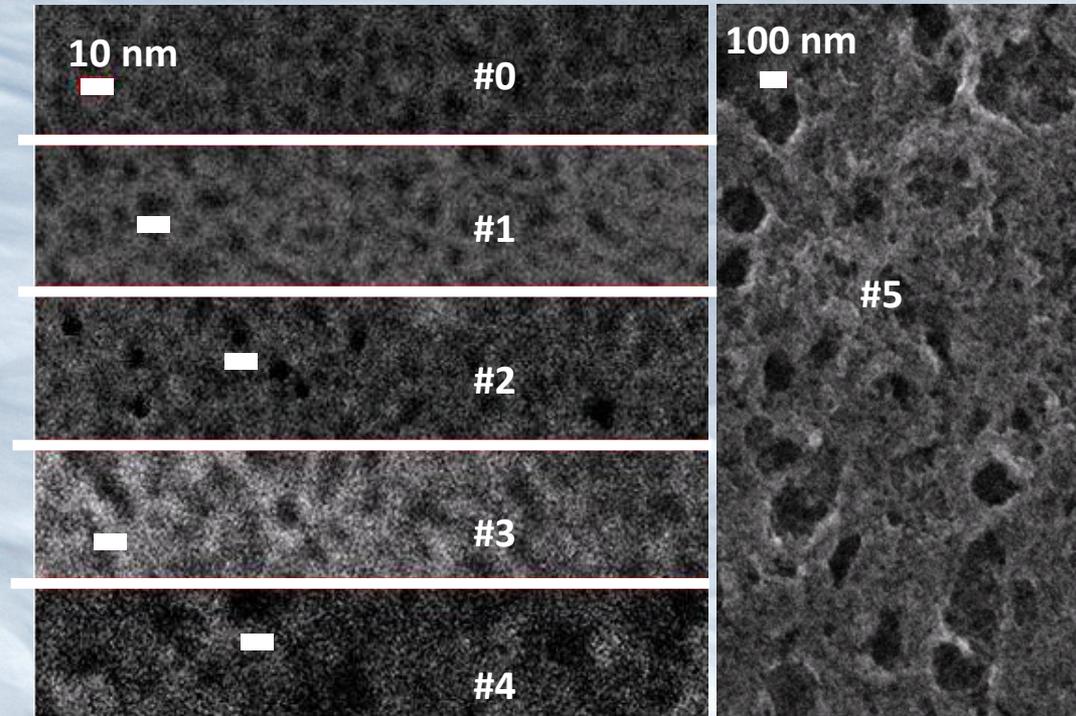
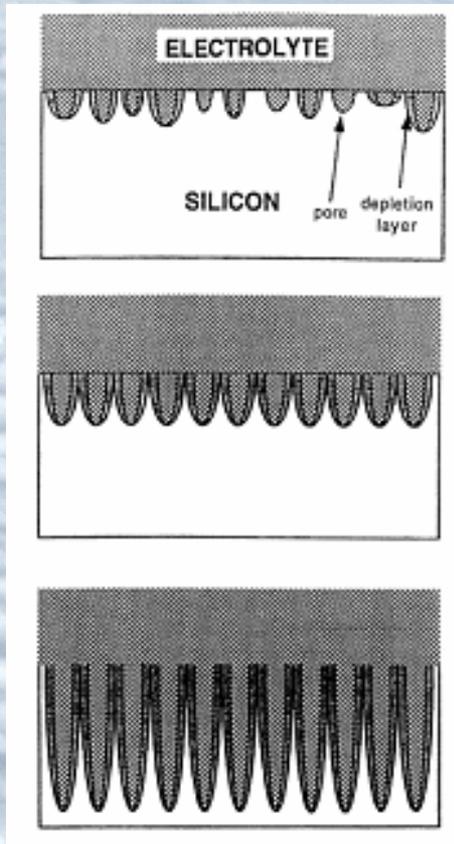
$$T = (2/3k_B)E_g$$

#0 (4-7 nm) mini T is 180-60 K
 #1 (8-12 nm) min T is 45-20 K



Tuning the size of nanochannels

produced by electrochemical etching, as for porous silicon but adapting times and current for obtaining nano-structures



Possibility of tuning: #0 = 4-7 nm

#1=8-12 nm #2= 8-14 nm

3= 10-16 nm #4= 14-20 nm

#5= 80-120 nm

Si p-type 0.15-0.21 Ohm/cm
current from 4-18 mA/cm² , 15'

Trento slow positron beam (50 eV-30 keV)

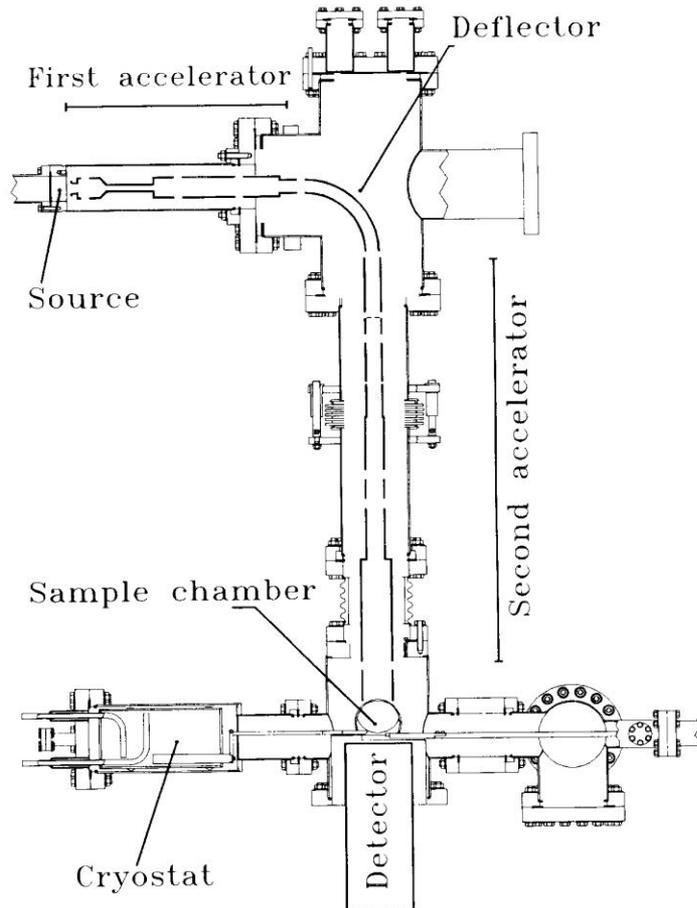
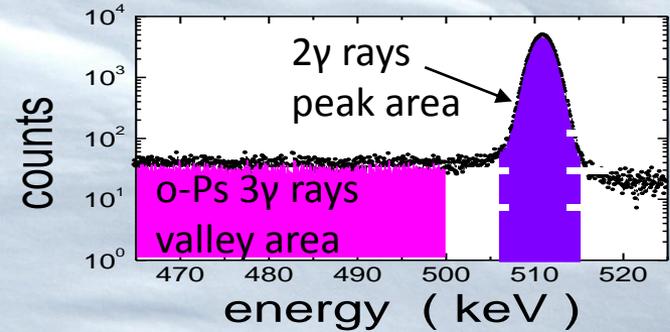
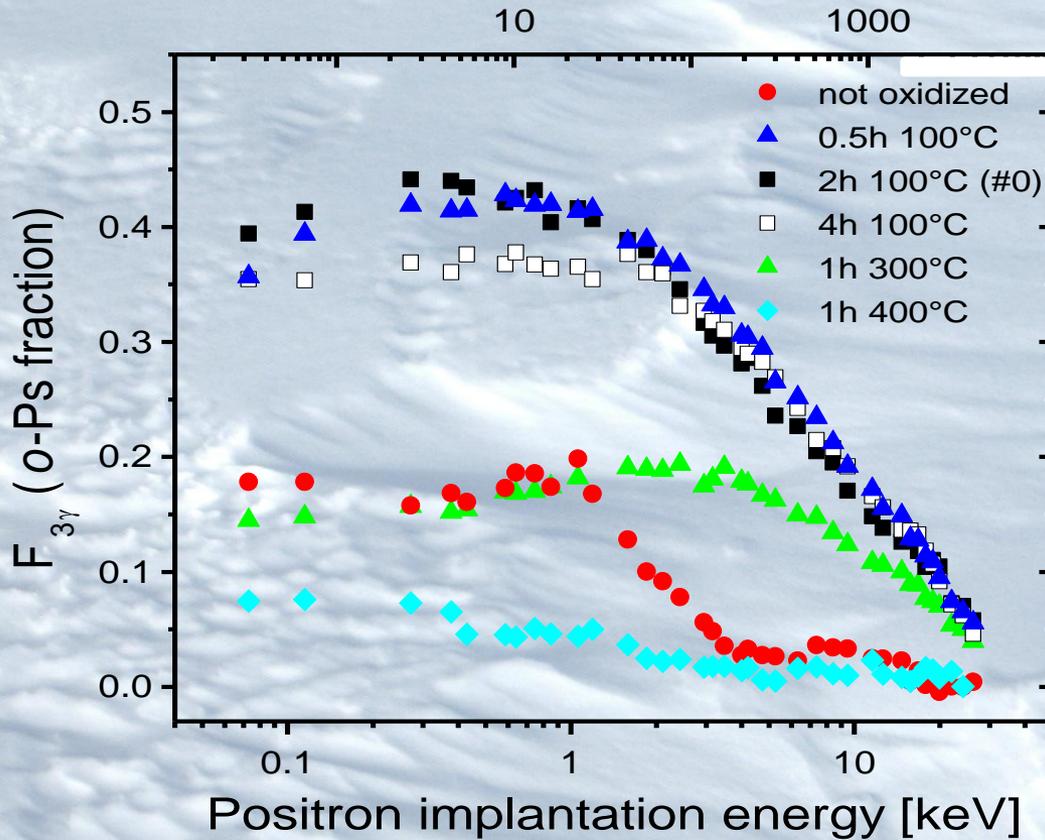


Fig. 1. A schematic layout of the electrostatic positron beam constructed in the Trento laboratory.



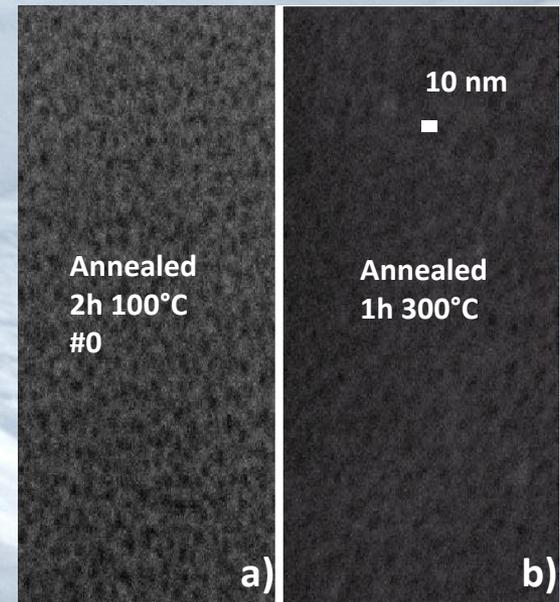
Optimum oxidation for the Ps yield

Mean positron implantation depth [nm]



$$R(E) = V(E) / P(E)$$

$$F_{3\gamma}(E) = \frac{3}{4} \left\{ 1 + \frac{P_1 [R_1 - R(E)]}{P_0 [R(E) - R_0]} \right\}$$



Ps yield and channel size

$$F_{3\gamma}(E) = A(E) \cdot B(E) + C(E)$$

$$A(E) = F_1 + (F_2 - F_1) e^{-\frac{1}{2} \left(\frac{E}{E_1} \right)^\beta}$$

o-Ps formation

$$B(E) = \frac{1}{1 + \left(\frac{E}{E_0} \right)^{1.6}}$$

o-Ps out diffusion probability

$$C(E) = K \left[\frac{C_1 - C_2}{1 + \left(\frac{E}{E_2} \right)} + C_2 \right]$$

o-Ps annihilation via 3γ into pores

#0 = 4-7 nm

#1=8-12 nm

#2= 8-14 nm

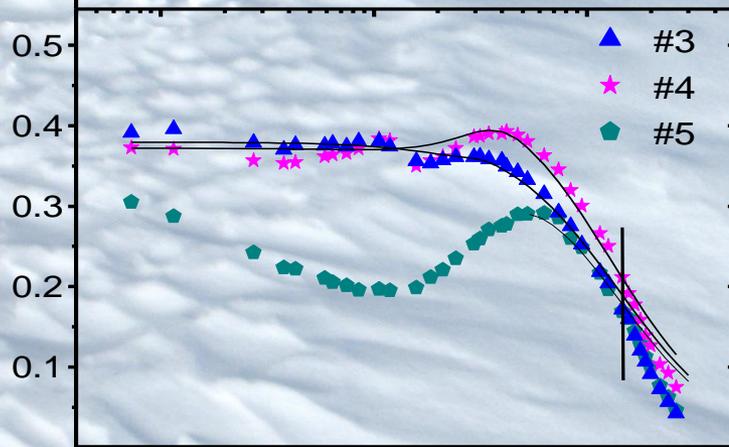
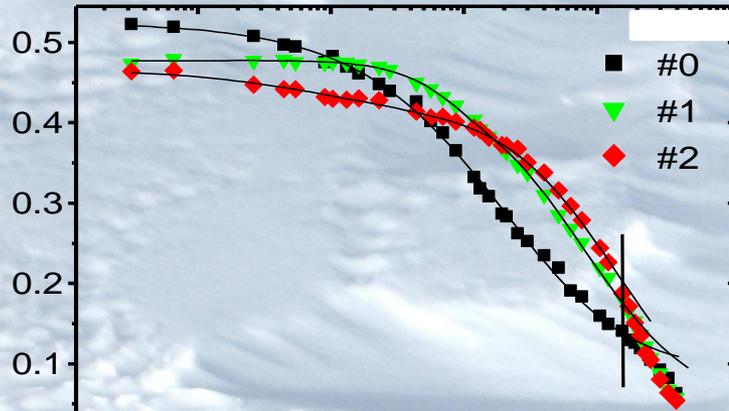
3= 10-16 nm

#4= 14-20 nm

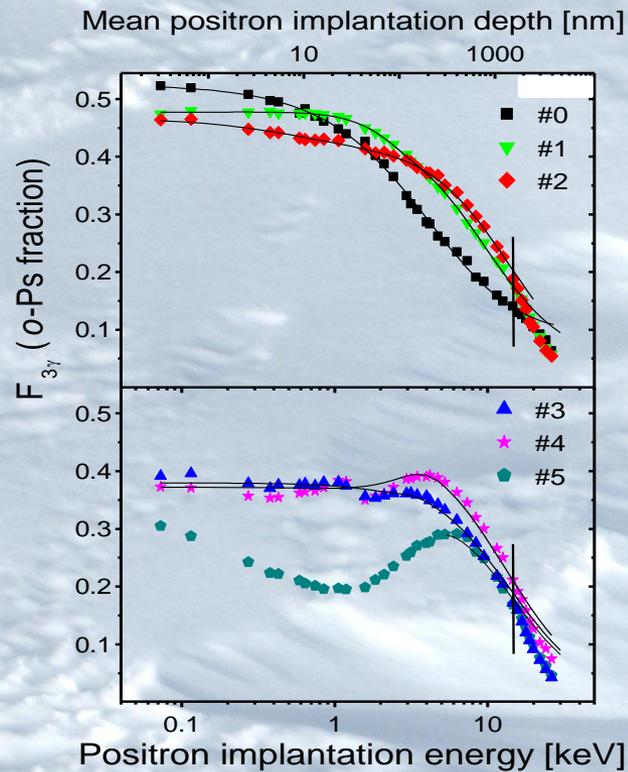
#5= 80-120 nm

Mean positron implantation depth [nm]

10 1000



Positron implantation energy [keV]



Up to 42 % of implanted positrons
at 1 keV emitted as o-Ps

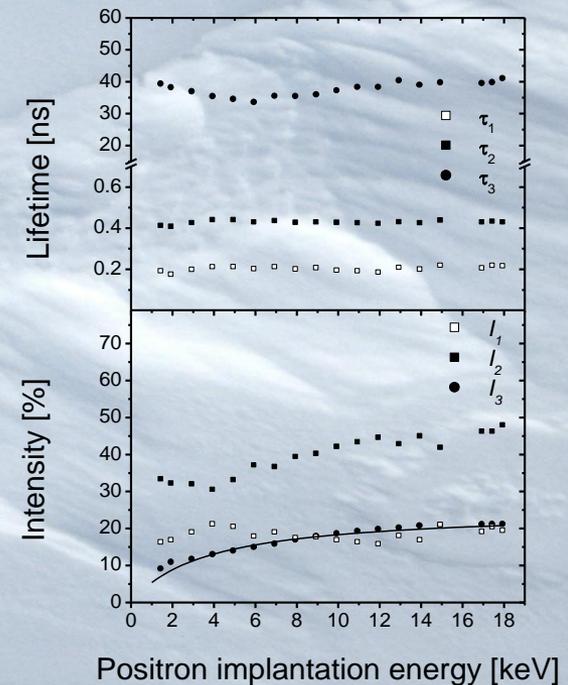
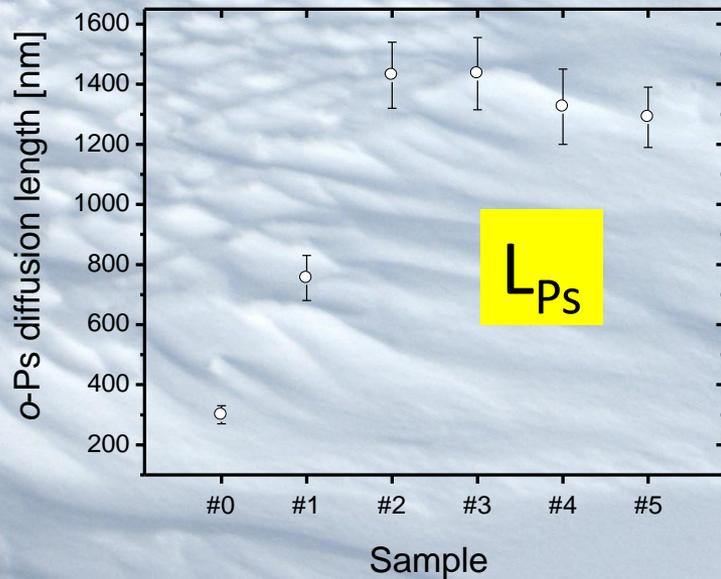
The o-Ps fraction out-diffusing at 10
keV positron implantation energy is
still

10 % in #0 = 4-7 nm

17 % in #1 = 8-12 nm

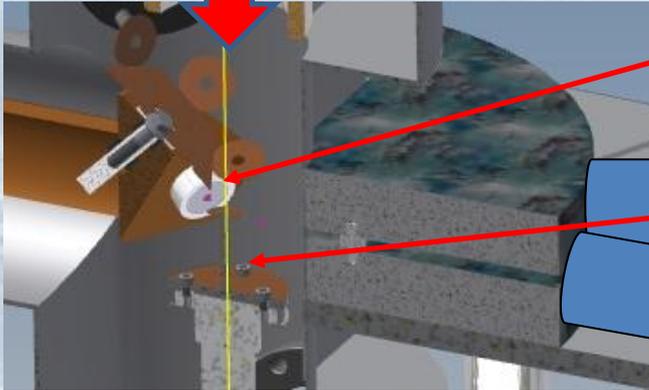
23-25 % in #2, #3, #4 and #5

15 - 100nm



Trento TOF Apparatus

BEAM

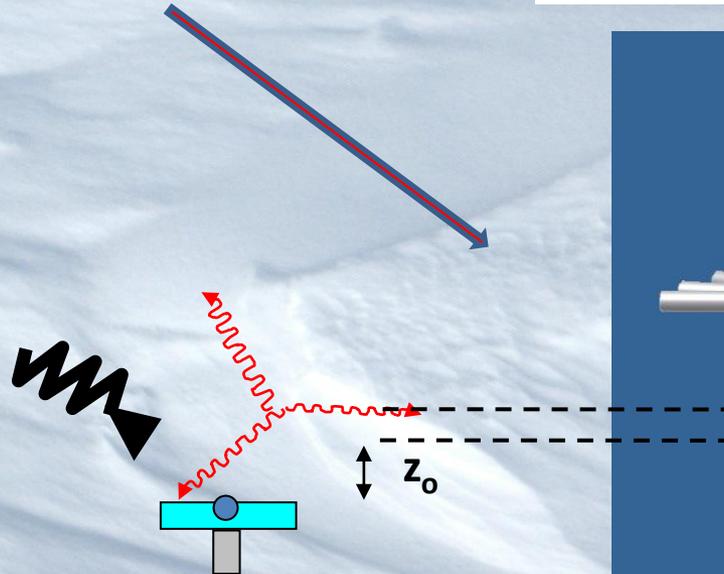
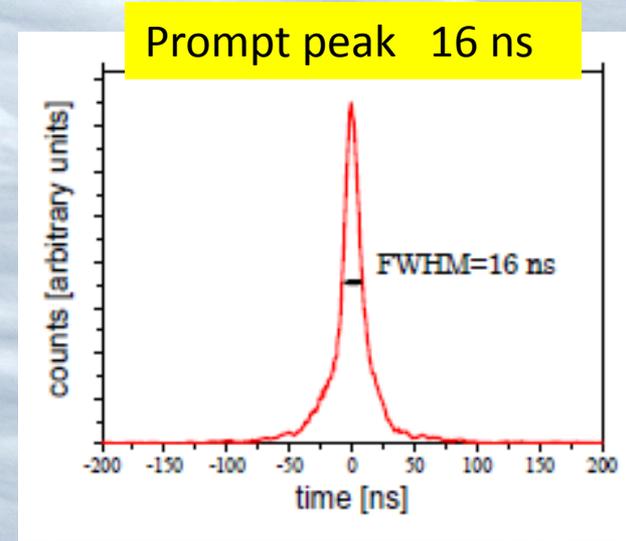


2 channeltrons

target position



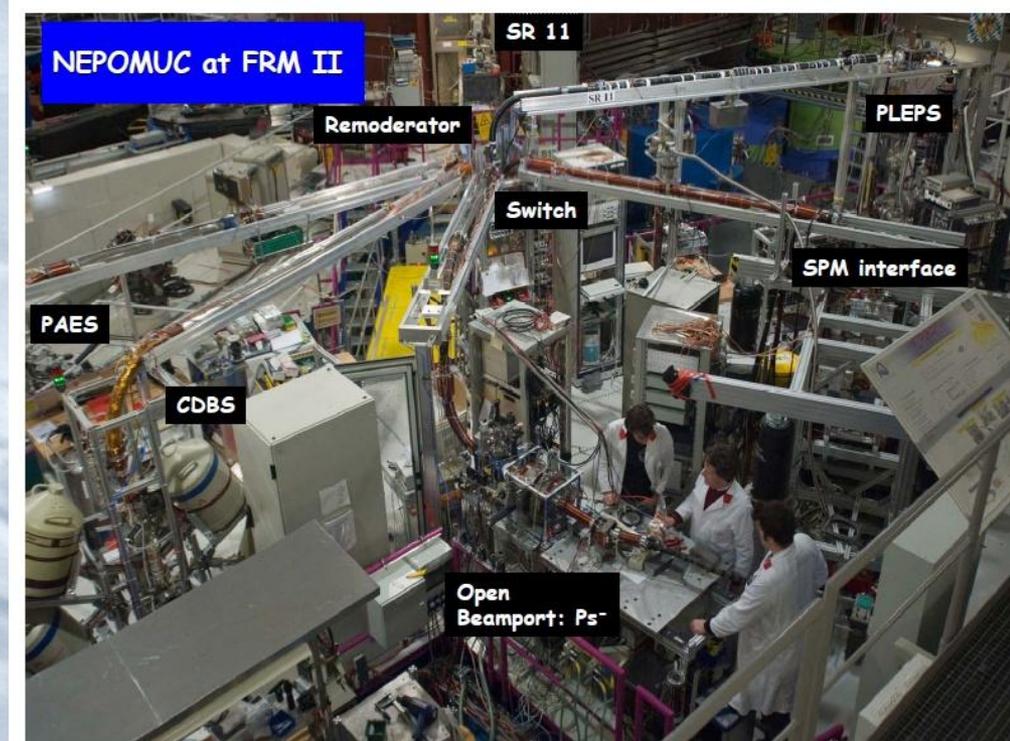
5 NaI scintillators



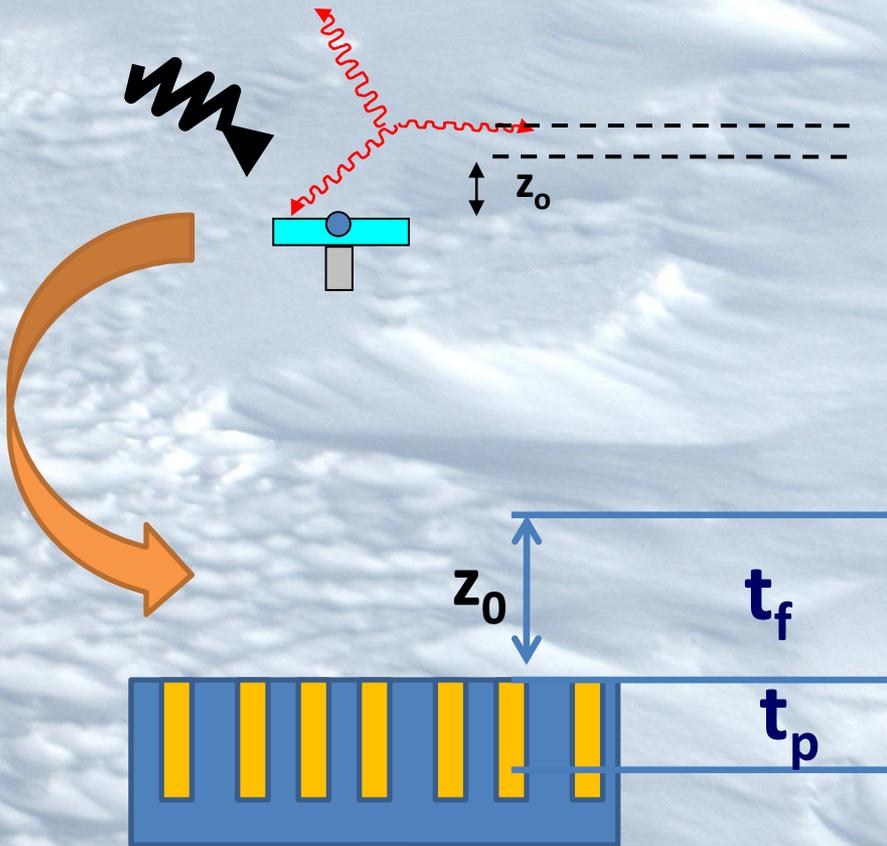


The TOF apparatus of Trento is now at the intense positron source NEPOMUC at the FRMII reactor in Munich and will be set up at the reactor hall in June-July.

NEPOMUC gives 10^9 e⁺ /s



o-Ps Time of Flight measurements



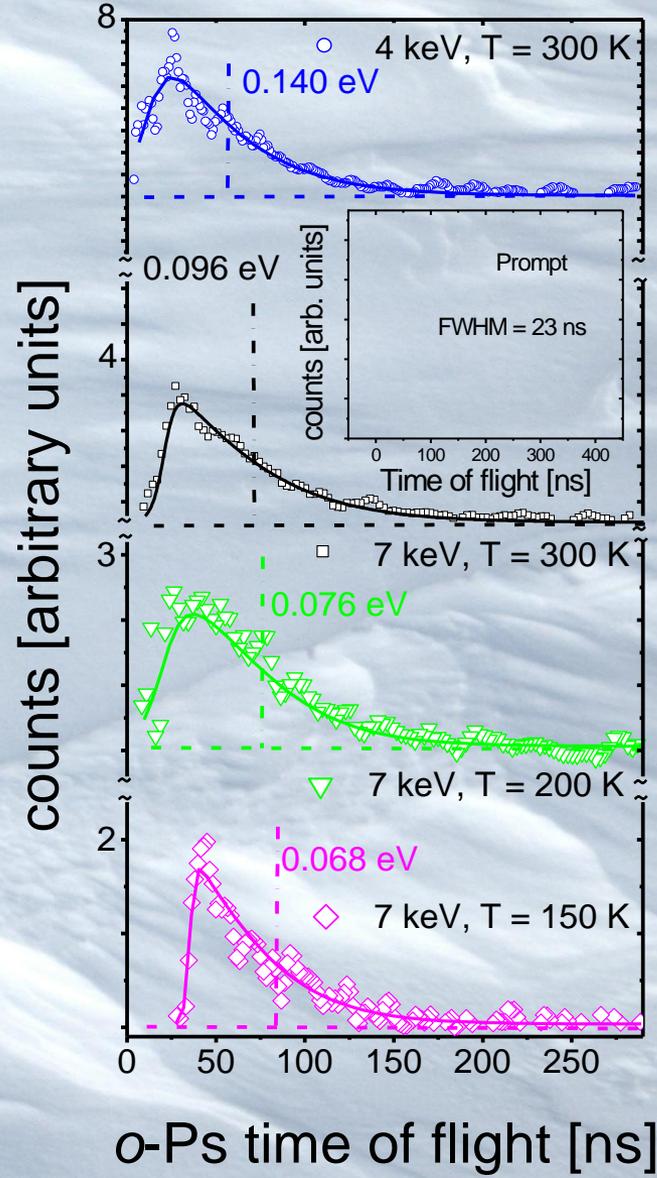
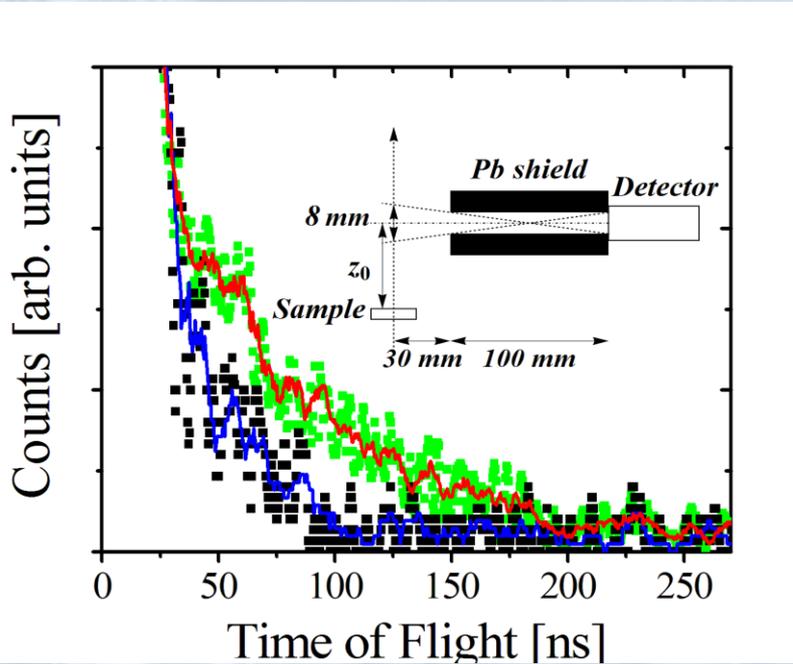
$$E_{\perp} = (m_0 z_0^2) / t_f^2$$

where $\langle t_m \rangle = \langle t_p \rangle + \langle t_f \rangle$

$$\langle t_m \rangle = \langle t_p \rangle + z_0 / v_{\perp}$$

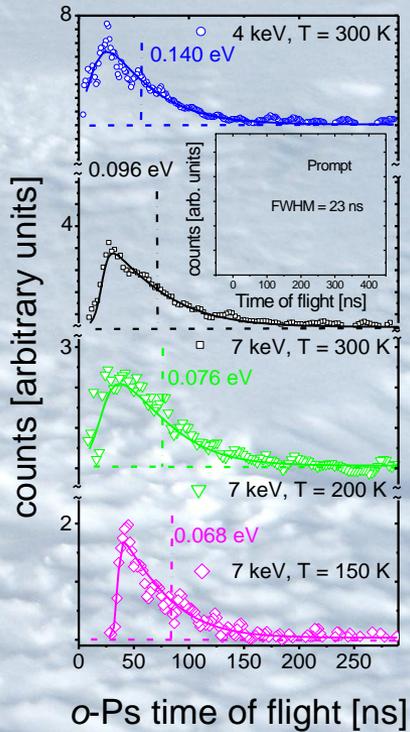
If $t_p \ll t_f$ $t_m \cong t_f$

Ps cooling - 5-8 nm channels



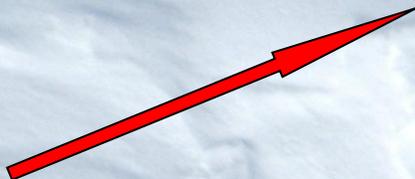
After smoothing, subtraction of the background, and correction by multiplying by $\left(\frac{1}{t}\right)\exp\left(\frac{t}{142}\right)$

Ps energy

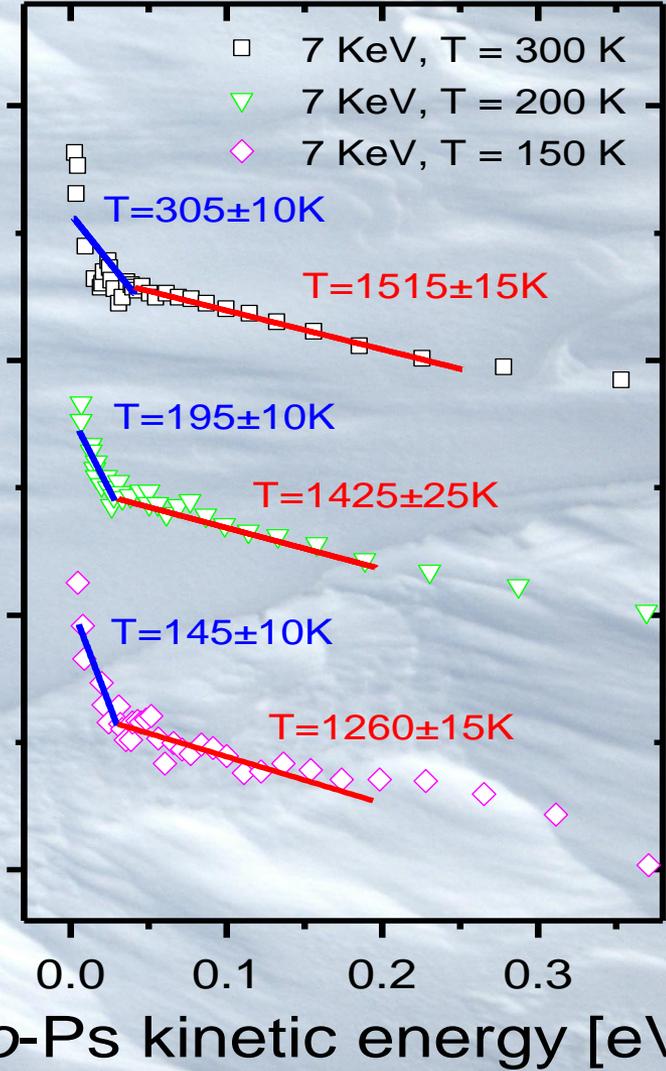


$$\int N(t)dt = \int N(E)dE$$

$$N(E) \propto N(t)t^3$$



log(dN/dE) [arbitrary units]



The two lines in log-lin graph are proportional to $e^{-\frac{E_{\perp}}{k_B T}}$

o-Ps kinetic energy [eV]

at two different T.

Analysis of the Ps energy spectra

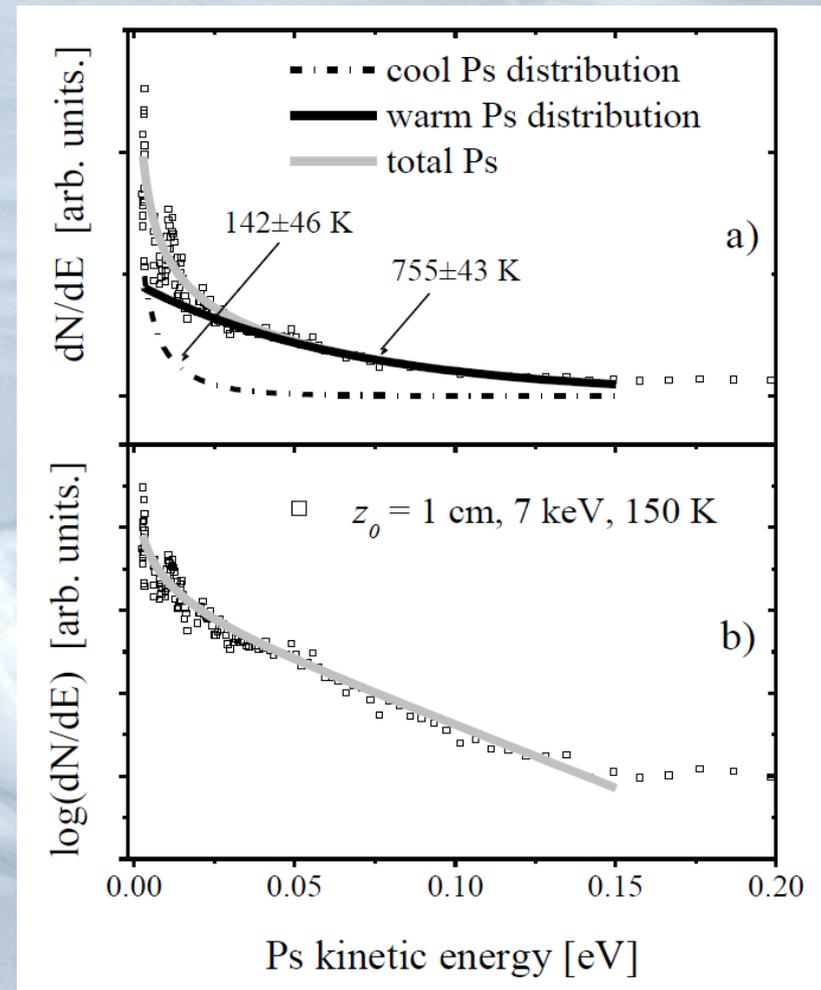
$$\ln \left(\frac{dN}{dE_{\perp}} \right) = \ln \left[\alpha \cdot E_{\perp}^m A(m, T_1) e^{-\frac{E_{\perp}}{k_B T_1}} + \beta \cdot E_{\perp}^n B(n, T_2) e^{-\frac{E_{\perp}}{k_B T_2}} \right]$$

With A and B, normalization factors

$$\int_0^{\infty} E_{\perp}^m A(m, T_1) e^{-\frac{E_{\perp}}{k_B T_1}} dE_{\perp} = 1$$

$$\int_0^{\infty} E_{\perp}^n B(n, T_2) e^{-\frac{E_{\perp}}{k_B T_2}} dE_{\perp} = 1$$

$$\alpha + \beta = 1$$



Cool distribution

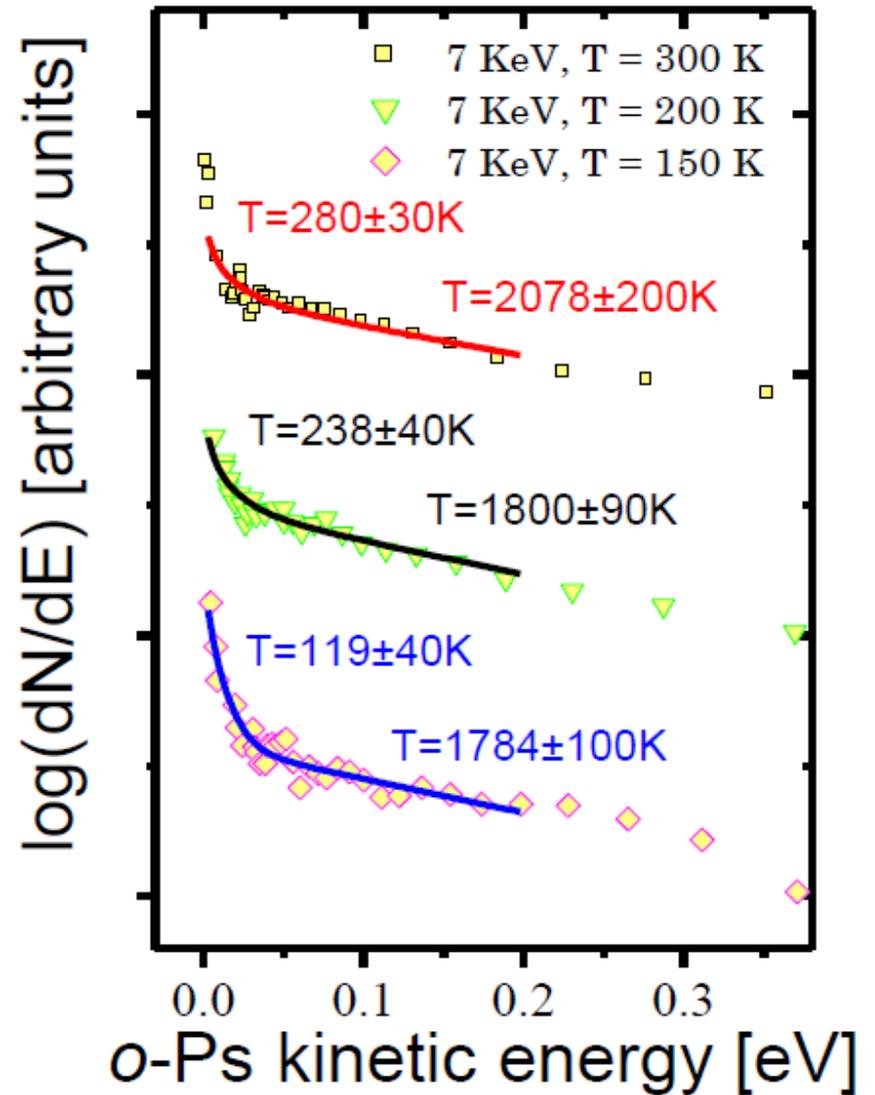
$$F(E_{c\perp}) = \frac{E_{\perp}^{-1/2}}{\sqrt{\pi k_B T_1}} e^{-\frac{E_{\perp}}{k_B T_1}}$$

$$\langle E_{c\perp} \rangle = \frac{T_1 k_B}{2}$$

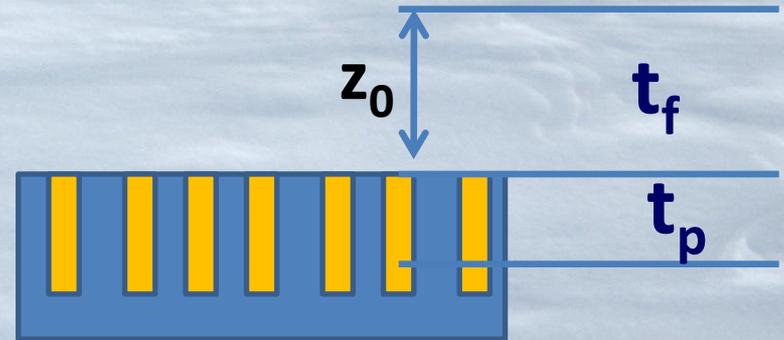
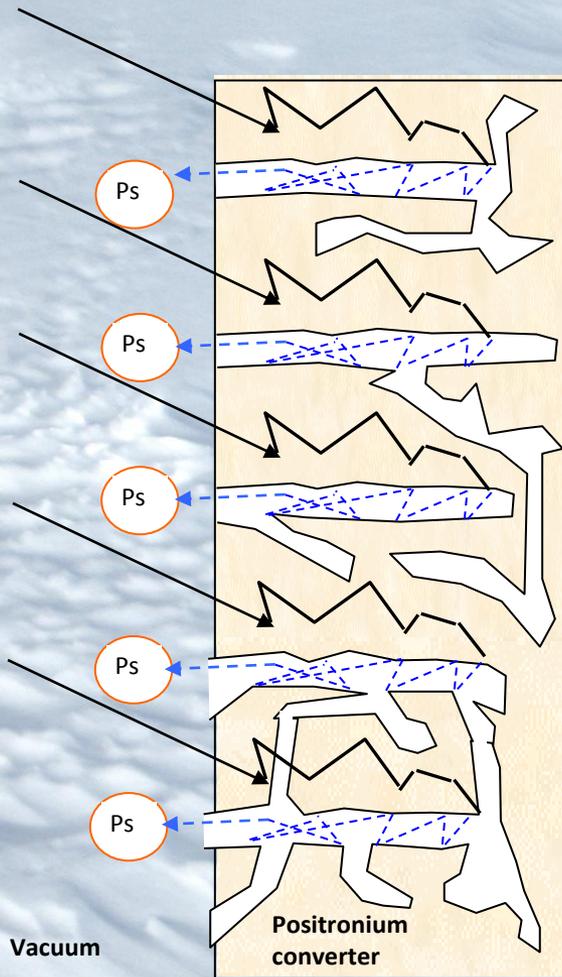
Warm distribution

$$G(E_{w\perp}) = \frac{1}{k_B T_2} e^{-\frac{E_{\perp}}{k_B T_2}}$$

$$\langle E_{w\perp} \rangle = T_2 k_B$$



Permanence time of Ps in nano-channels before escaping into vacuum

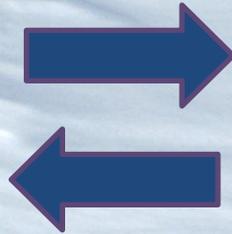
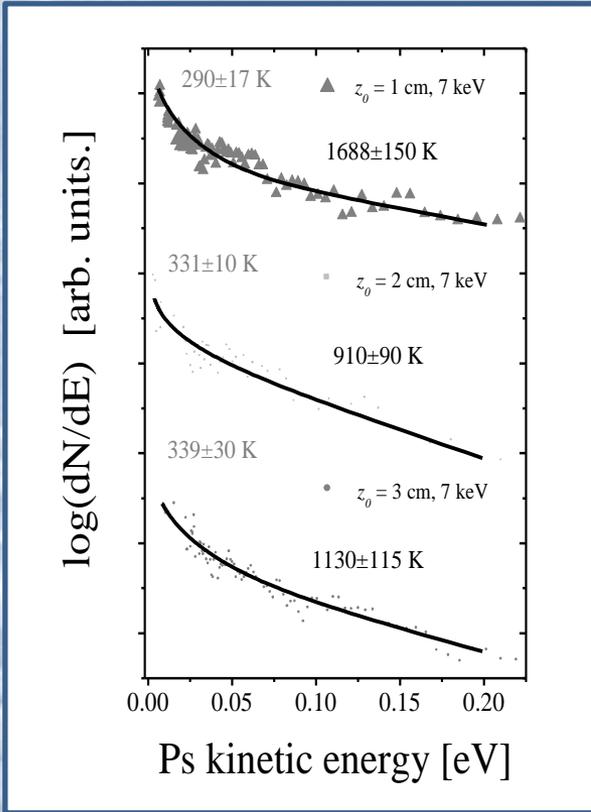


$$\langle t_m \rangle = \langle t_p \rangle + \langle t_f \rangle$$

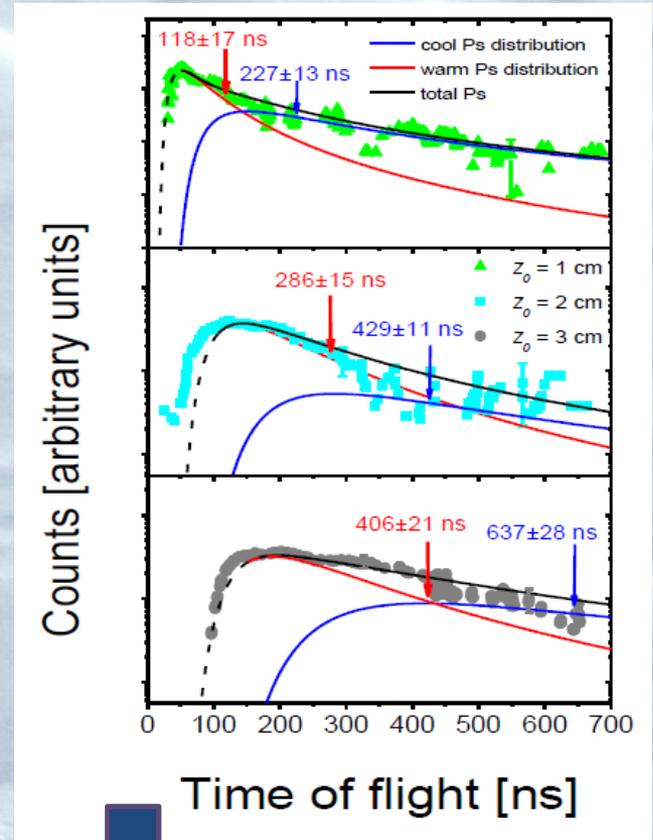
Measurements at three different distances z_0 allow to evaluate $\langle t_p \rangle$

Measurements were done at 7 keV e^+ energy

Ps energy spectra



Ps energy spectra

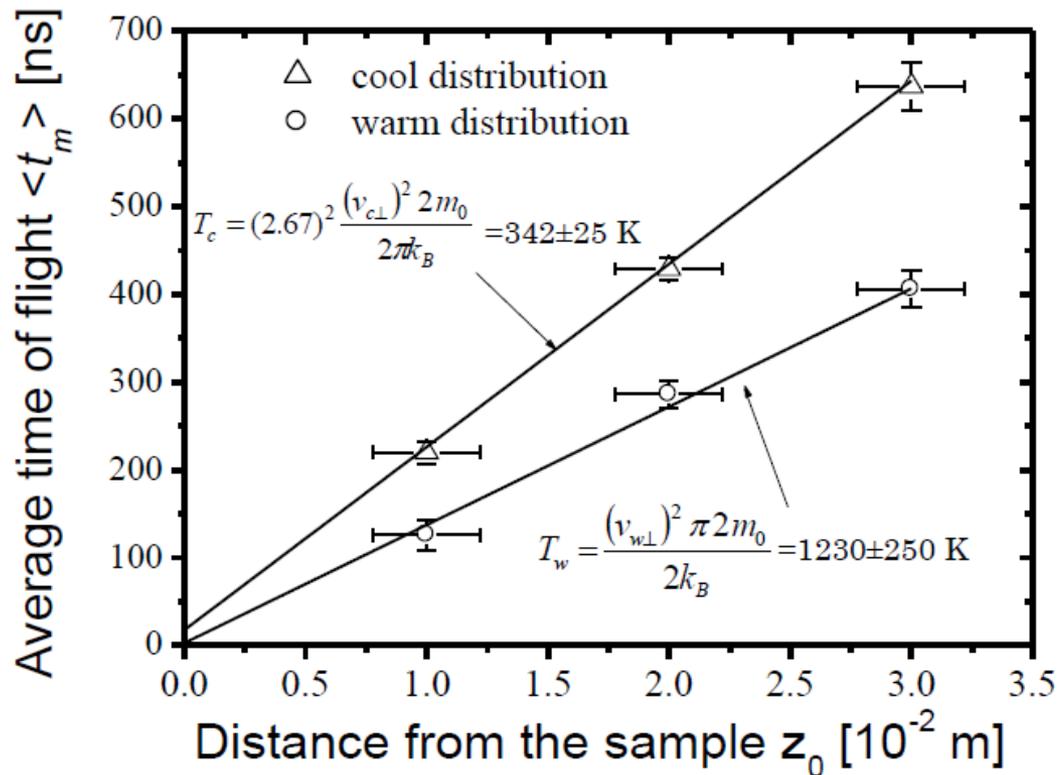


$$F(E_{c\perp}) = \frac{E_{\perp}^{-1/2}}{\sqrt{\pi k_B T_1}} e^{-\frac{E_{\perp}}{k_B T_1}}$$

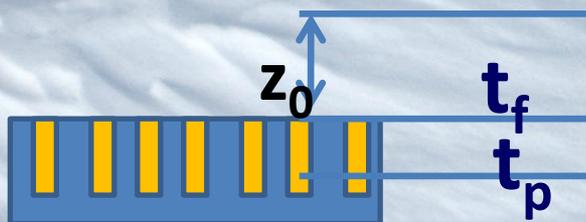
$$G(E_{w\perp}) = \frac{1}{k_B T_2} e^{-\frac{E_{\perp}}{k_B T_2}}$$

$\langle t_m \rangle$ of the cold and warm distribution

Cooling time of Ps



$$\langle t_m \rangle = \langle t_p \rangle + z_0 / v_{\perp}$$



$$\langle t_{cp} \rangle = 18 \pm 6 \text{ ns}$$

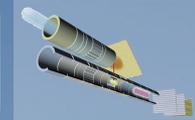
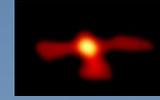
$$\langle t_{cw} \rangle < 7 \text{ ns}$$

conclusion with a question

Study of Ps formation and annihilation in complex materials and porous complex materials at low temperature are lacking

Could be more data useful for understanding signal of Ps annihilation in ISM ?

Thanks for listening and
Thanks to the organizers
for the invitation and
the wonderful workshop



From Schilthorn